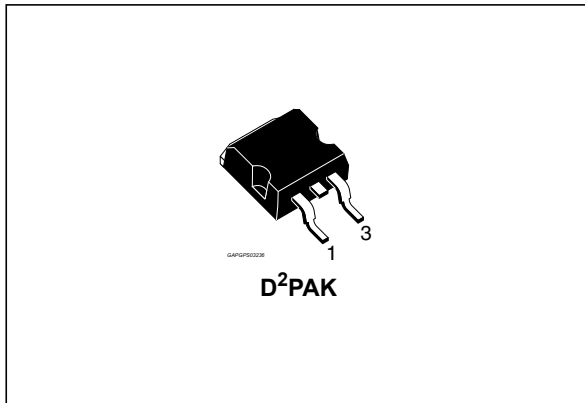


OMNIFET II fully autoprotected Power MOSFET

Datasheet - production data



- Aerospace and Defense features
 - Dedicated traceability and part marking
 - Production parts approval documents available
 - Adapted Extended life time and obsolescence management
 - Extended Product Change Notification process
 - Designed and manufactured to meet sub ppm quality goals
 - Advanced mold and frame designs for Superior resilience to harsh environment (acceleration, EMI, thermal, humidity)
 - Single Fabrication, Assembly and Test site
 - Dual internal production source capability

Features

Type	$R_{DS(on)}$	I_{lim}	V_{clamp}
RVNB35NV04	10 m Ω	30 A	40 V

- Linear current limitation
- Thermal shutdown
- Short circuit protection
- Integrated clamp
- Low current drawn from input pin
- Diagnostic feedback through input pin
- ESD protection
- Direct access to the gate of the Power MOSFET (analog driving)
- Compatible with standard Power MOSFET

Application

All types of resistive, inductive and capacitive loads in Aerospace and Defense applications

Description

The RVNB35NV04 is a monolithic device designed in STMicroelectronics® VIPower® M0-3 Technology, intended for replacement of standard Power MOSFETs from DC up to 25 kHz applications.

Built-in thermal shutdown, linear current limitation and overvoltage clamp protect the chip in harsh environments. Fault feedback can be detected by monitoring the voltage at the input pin.

Table 1. Device summary

Package	Order codes	
	Tube	Tape and reel
D ² PAK	RVNB35NV04	RVNB35NV04TR

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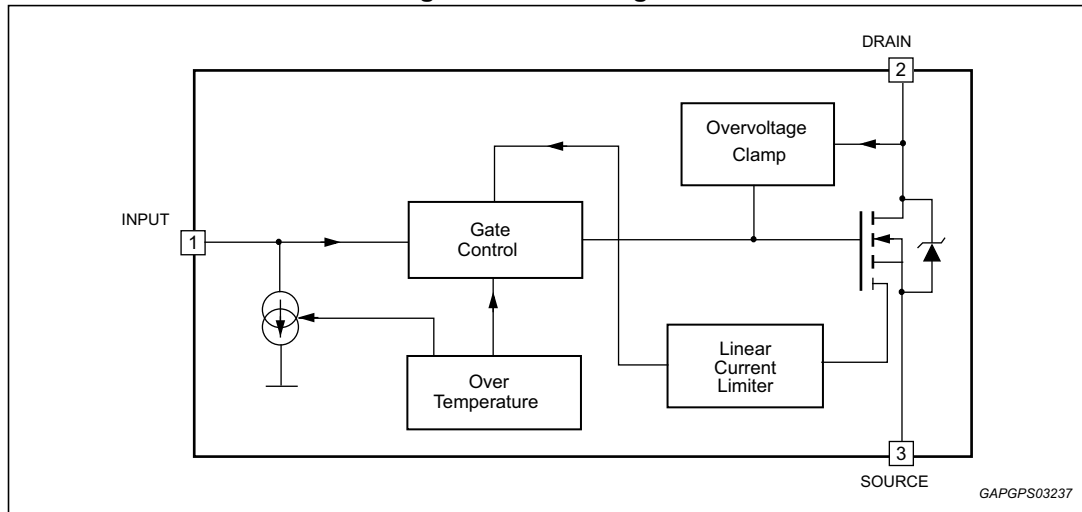
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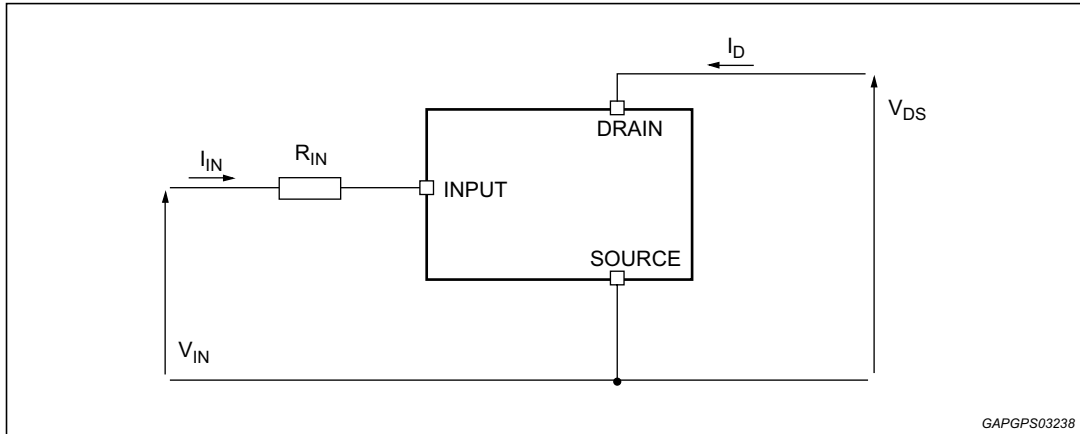
1 Block diagram and pin connection

Figure 1. Block diagram



2 Electrical specification

Figure 2. Current and voltage conventions



2.1 Absolute maximum ratings

Stressing the device above the rating listed in *Table 2* may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to the conditions in table below for extended periods may affect device reliability

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{IN} = 0\text{ V}$)	Internally clamped	V
V_{IN}	Input voltage	Internally clamped	V
I_{IN}	Input current	± 20	mA
$R_{IN\text{ MIN}}$	Minimum input series impedance	4.7	Ω
I_D	Drain current	Internally limited	A
I_R	Reverse DC output current	-30	A
V_{ESD1}	Electrostatic discharge ($R = 1.5\text{ k}\Omega$, $C = 100\text{ pF}$)	4000	V
V_{ESD2}	Electrostatic discharge on output pin only ($R = 330\ \Omega$, $C = 150\text{ pF}$)	16500	V
P_{tot}	Total dissipation at $T_C = 25^\circ\text{C}$	125	W
T_J	Operating junction temperature	Internally limited	$^\circ\text{C}$
T_C	Case operating temperature	Internally limited	$^\circ\text{C}$
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$

2.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (max)	1	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient (max)	50 ⁽¹⁾	°C/W

1. When mounted on a standard single-sided FR4 board with 50mm² of Cu (at least 35 mm thick) connected to all DRAIN pins.

2.3 Electrical characteristics

-40°C < T_j < 150°C, unless otherwise specified.

Table 4. Off

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V_{CLAMP}	Drain-source clamp voltage	$V_{IN} = 0\text{ V}; I_D = 15\text{ A}$	40	45	55	V
V_{CLTH}	Drain-source clamp threshold voltage	$V_{IN} = 0\text{ V}; I_D = 2\text{ mA}$	36			V
V_{INTH}	Input threshold voltage	$V_{DS} = V_{IN}; I_D = 1\text{ mA}$	0.5		2.5	V
I_{ISS}	Supply current from input pin	$V_{DS} = 0\text{ V}; V_{IN} = 5\text{ V}$		100	150	μA
V_{INCL}	Input-source clamp voltage	$I_{IN} = 1\text{ mA}$	6	6.8	8	V
		$I_{IN} = -1\text{ mA}$	-1.0		-0.3	V
I_{DSS}	Zero input voltage drain current ($V_{IN} = 0\text{ V}$)	$V_{DS} = 13\text{ V}; V_{IN} = 0\text{ V}; T_j = 25\text{ °C}$			30	μA
		$V_{DS} = 25\text{ V}; V_{IN} = 0\text{ V}$			75	μA

Table 5. On

Symbol	Parameter	Test conditions	Max	Unit
$R_{DS(on)}$	Static drain-source on resistance	$V_{IN} = 5\text{ V}; I_D = 15\text{ A}; T_j = 25\text{ °C}$	13	mΩ
		$V_{IN} = 5\text{ V}; I_D = 15\text{ A}; T_j = 150\text{ °C}$	24	mΩ

$T_j = 25\text{ °C}$, unless otherwise specified.

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DD} = 13\text{ V}; I_D = 15\text{ A}$	—	35	—	S
C_{OSS}	Output capacitance	$V_{DS} = 13\text{ V}; f = 1\text{ MHz}; V_{IN} = 0\text{ V}$	—	1300	—	pF

1. Pulsed: Pulse duration = 300 ms, duty cycle 1.5%

Table 7. Switching

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 15\text{ V}; I_D = 15\text{ A};$ $V_{gen} = 5\text{ V};$ $R_{gen} = R_{IN\text{ MIN}} = 4.7\ \Omega$ (see Figure 2)	—	150	500	ns
t_r	Rise time		—	840	2500	ns
$t_{d(off)}$	Turn-off delay time		—	980	3000	ns
t_f	Fall time		—	600	1500	ns
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 15\text{ V}; I_D = 15\text{ A};$ $V_{gen} = 5\text{ V}; R_{gen} = 2.2\text{ k}\Omega$ (see Figure 2)	—	4	12	μs
t_r	Rise time		—	27	100	μs
$t_{d(off)}$	Turn-off delay time		—	34	120	μs
t_f	Fall time		—	31	110	μs
$(di/dt)_{on}$	Turn-on current slope	$V_{DD} = 15\text{ V}; I_D = 15\text{ A}; V_{gen} = 5\text{ V};$ $R_{gen} = R_{IN\text{ MIN}} = 4.7\ \Omega$	—	18		$\text{A}/\mu\text{s}$
Q_i	Total input charge	$V_{DD} = 12\text{ V}; I_D = 15\text{ A}; V_{IN} = 5\text{ V};$ $I_{gen} = 2.13\text{ mA}$ (see Figure 7)	—	118		nC

Table 8. Source drain diode

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 15\text{ A}; V_{IN} = 0\text{ V}$	—	0.8	—	V
t_{rr}	Reverse recovery time	$I_{SD} = 15\text{ A}; di/dt = 100\text{ A}/\mu\text{s};$ $V_{DD} = 30\text{ V}; L = 200\ \mu\text{H}$ (see Figure 3)	—	400	—	ns
Q_{rr}	Reverse recovery charge		—	1.4	—	μC
I_{RRM}	Reverse recovery current		—	7	—	A

1. Pulsed: Pulse duration = 300 ms, duty cycle 1.5%

Table 9. Protections ($-40^\circ\text{C} < T_j < 150^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I_{lim}	Drain current limit	$V_{IN} = 6\text{ V}; V_{DS} = 13\text{ V}$	30	45	60	A
t_{dlim}	Step response current limit	$V_{IN} = 6\text{ V}; V_{DS} = 13\text{ V}$		50		μs
T_{jsh}	Overtemperature shutdown		150	175	200	$^\circ\text{C}$
T_{jrs}	Overtemperature reset		135			$^\circ\text{C}$
I_{gf}	Fault Sink Current	$V_{IN} = 5\text{ V}; V_{DS} = 13\text{ V}; T_j = T_{jsh}$	10	15	20	mA
E_{as}	Single pulse avalanche energy	Starting $T_j = 25^\circ\text{C}; V_{DD} = 24\text{ V};$ $V_{IN} = 5\text{ V};$ $R_{gen} = R_{IN\text{ MIN}} = 4.7\ \Omega;$ $L = 24\text{ mH}$ (see Figure 5 and Figure 6)	1.7			J

2.4 Protection features

During normal operation, the INPUT pin is electrically connected to the gate of the internal power MOSFET through a low impedance path.

The device then behaves like a standard power MOSFET and can be used as a switch from DC up to 25 KHz. The only difference from the user's standpoint is that a small DC current I_{ISS} (typ. 100 μ A) flows into the INPUT pin in order to supply the internal circuitry.

The device integrates:

- **Overvoltage clamp protection:**
internally set at 45 V, along with the rugged avalanche characteristics of the Power MOSFET stage give this device unrivalled ruggedness and energy handling capability. This feature is mainly important when driving inductive loads.
- **Linear current limiter circuit:**
limits the drain current I_D to I_{lim} whatever the INPUT pin voltages is. When the current limiter is active, the device operates in the linear region, so power dissipation may exceed the capability of the heatsink. Both case and junction temperatures increase, and if this phase lasts long enough, junction temperature may reach the overtemperature threshold T_{jsh} .
- **Overtemperature and short circuit protection:**
these are based on sensing the chip temperature and are not dependent on the input voltage. The location of the sensing element on the chip in the power stage area ensures fast, accurate detection of the junction temperature. Overtemperature cutout occurs in the range 150°C to 190°C, a typical value being 170°C. The device is automatically restarted when the chip temperature falls of about 15°C below shutdown temperature.
- **Status feedback:**
in the case of an overtemperature fault condition ($T_j > T_{jsh}$), the device tries to sink a diagnostic current I_{gf} through the INPUT pin in order to indicate fault condition. If driven from a low impedance source, this current may be used in order to warn the control circuit of a device shutdown. If the drive impedance is high enough so that the INPUT pin driver is not able to supply the current I_{gf} , the INPUT pin falls to 0 V. This does not however affect the device operation: no requirement is put on the current capability of the INPUT pin driver except to be able to supply the normal operation drive current I_{ISS} .

Additional features of this device are ESD protection according to the Human Body model and the ability to be driven from a TTL Logic circuit.

Figure 3. Switching time test circuit for resistive load

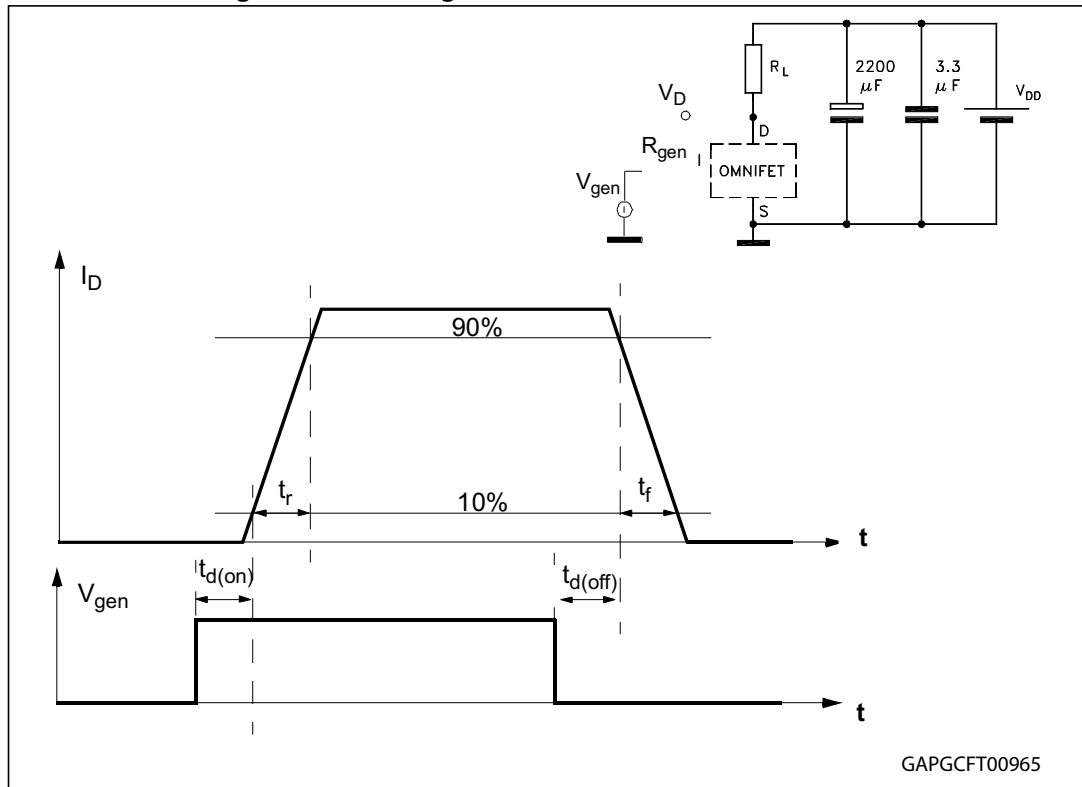


Figure 4. Test circuit for diode recovery times

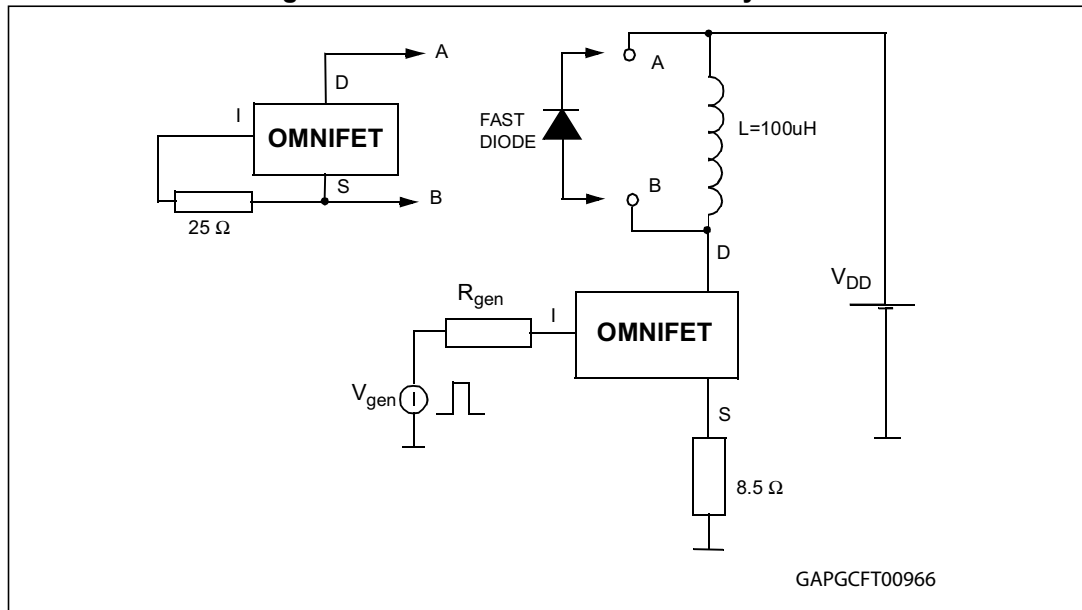


Figure 5. Unclamped inductive load test circuits

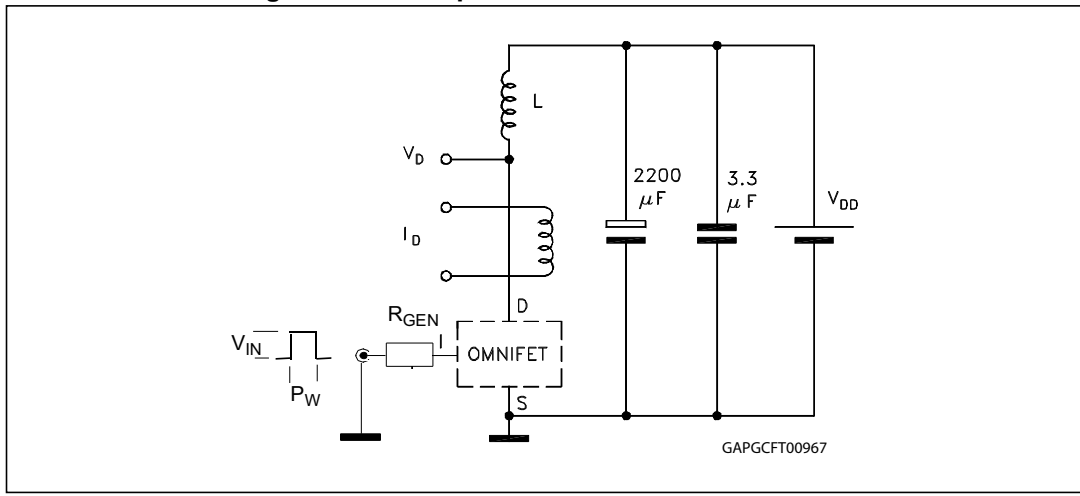


Figure 6. Unclamped inductive waveforms

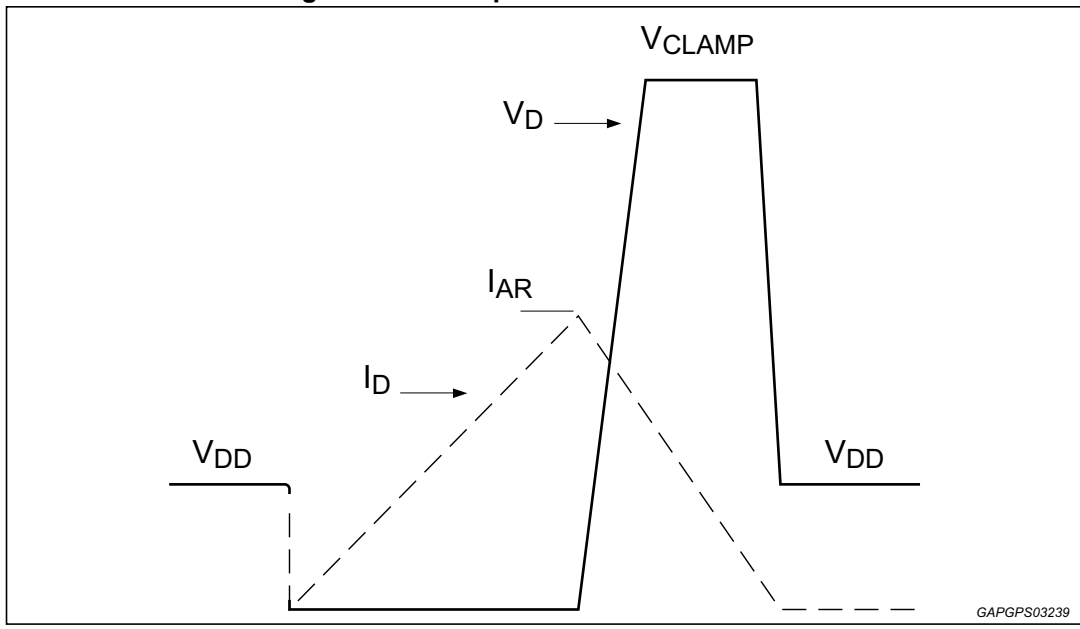
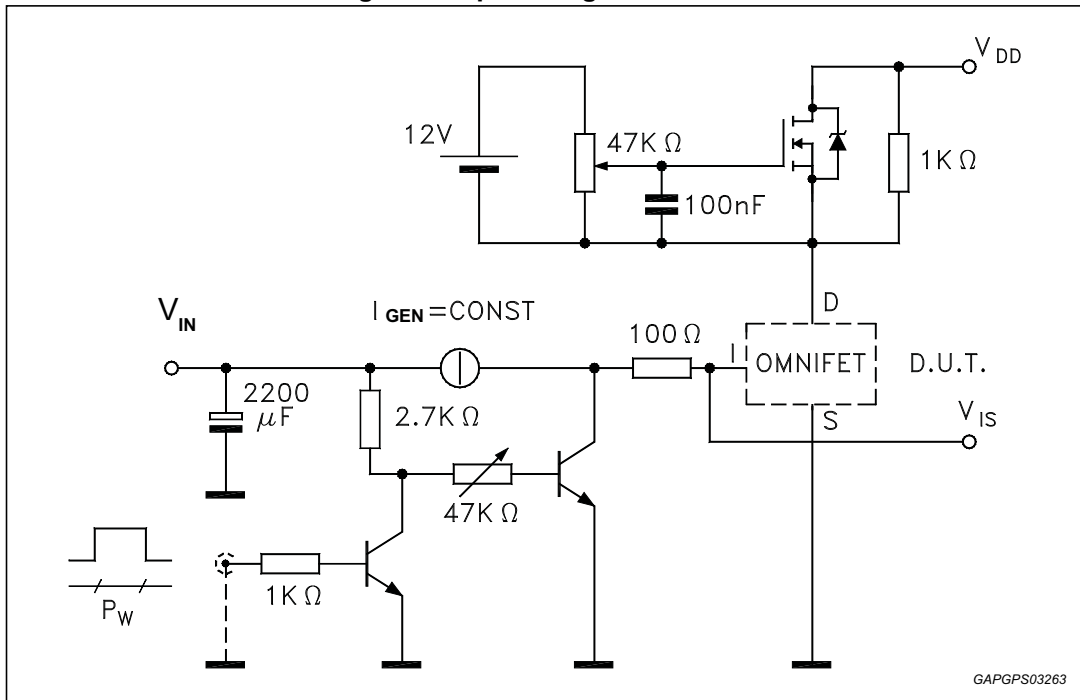
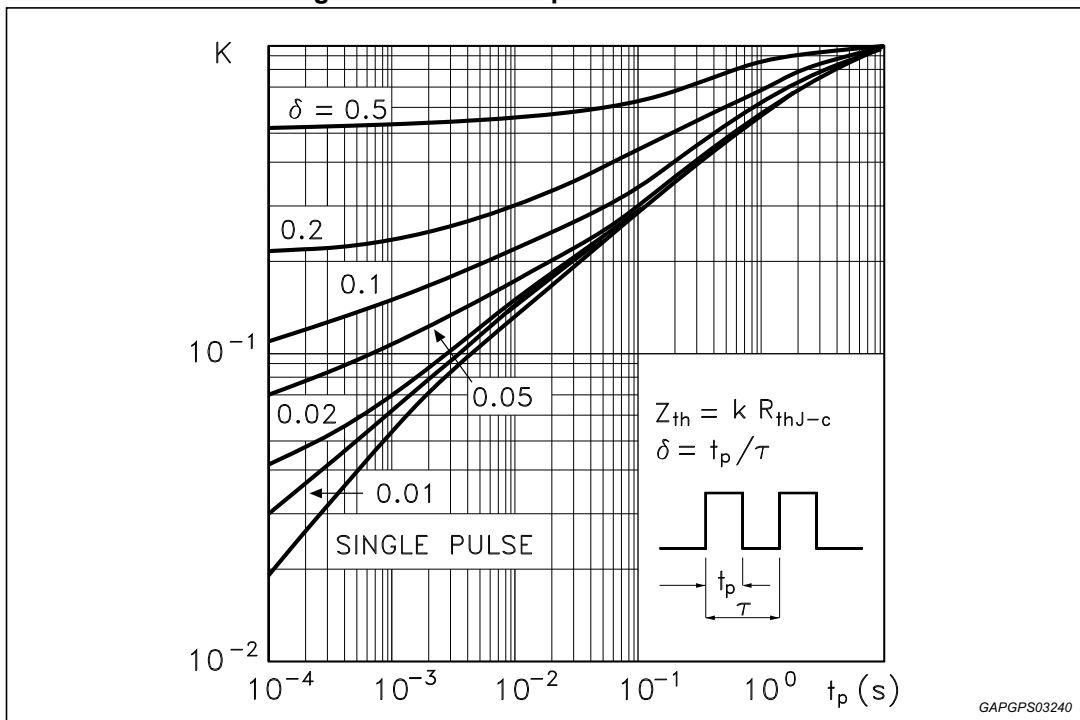


Figure 7. Input charge test circuit



GAPGPS03263

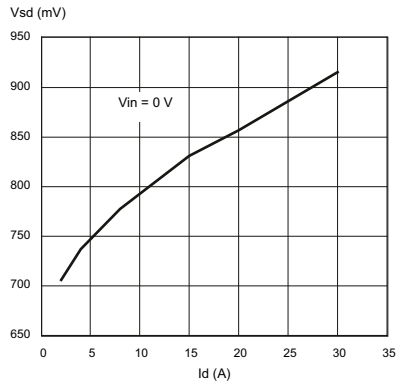
Figure 8. Thermal impedance for TO-220



GAPGPS03240

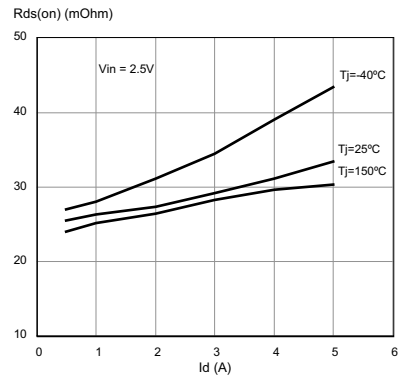
2.5 Electrical characteristics curves

Figure 9. Source-drain diode forward characteristics



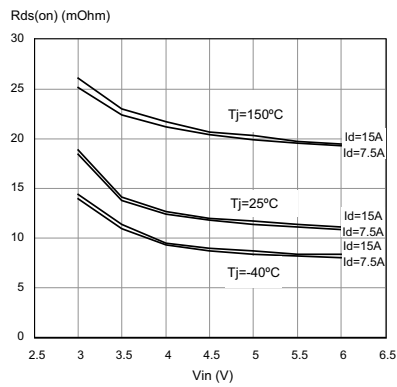
GAPGPS032

Figure 10. Static drain source on resistance



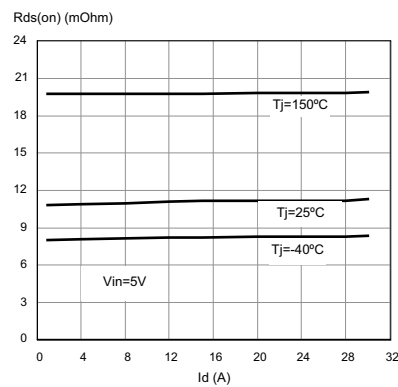
GAPGPS03241

Figure 11. Static drain-source on resistance vs. input voltage



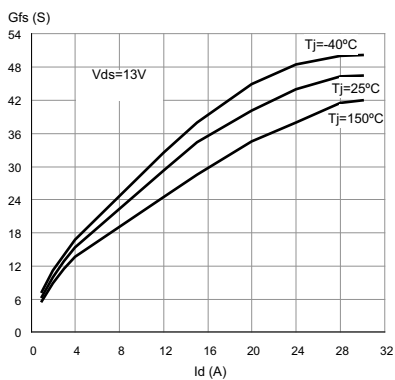
GAPGPS

Figure 12. Static drain-source on resistance vs. id



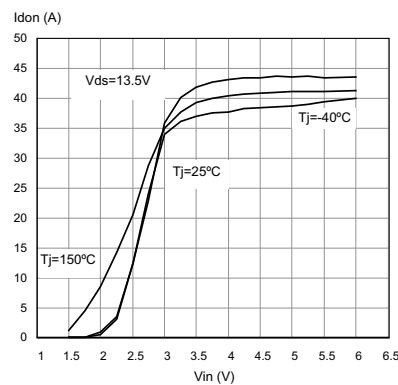
GAPGPS03

Figure 13. Transconductance



GAPGPS032

Figure 14. Transfer characteristics



GAPGPS03



Figure 15. Output characteristics

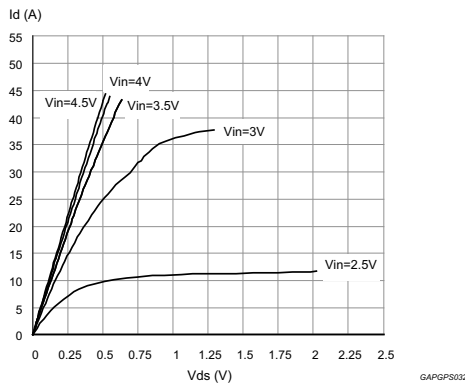


Figure 16. Normalized on resistance vs. temperature

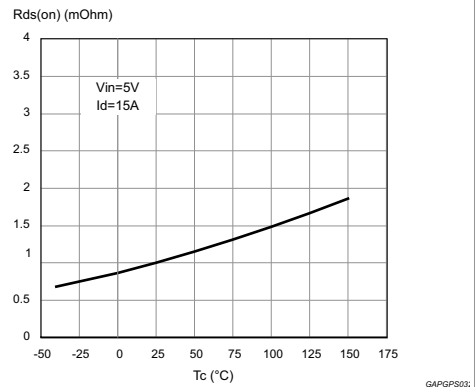


Figure 17. Turn-on current slope, $V_{IN} = 5 V$

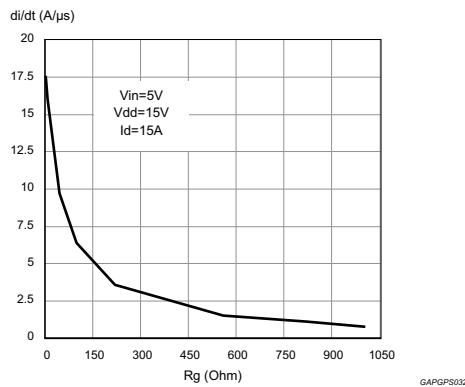


Figure 18. Turn-on current slope, $V_{IN} = 3.5 V$

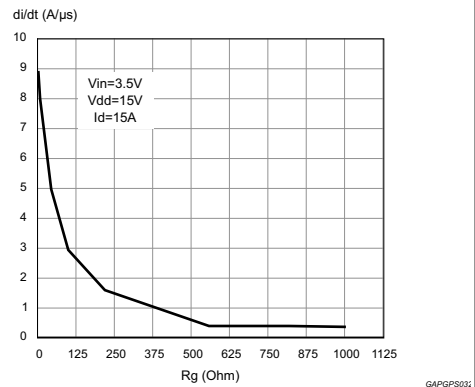


Figure 19. Input voltage vs. input charge

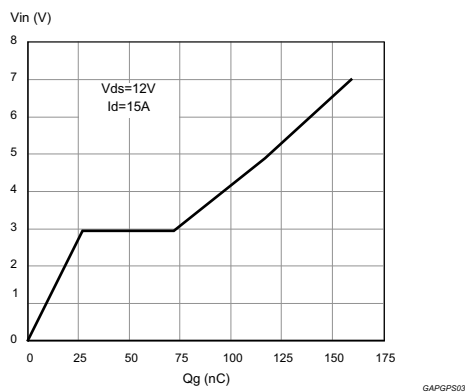


Figure 20. Turn off drain source voltage slope, $V_{IN} = 5 V$

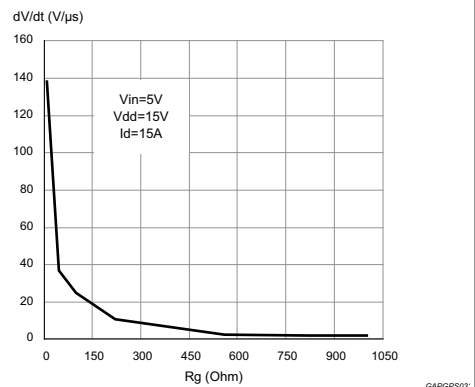


Figure 21. Turn off drain-source voltage slope, $V_{IN} = 3.5\text{ V}$

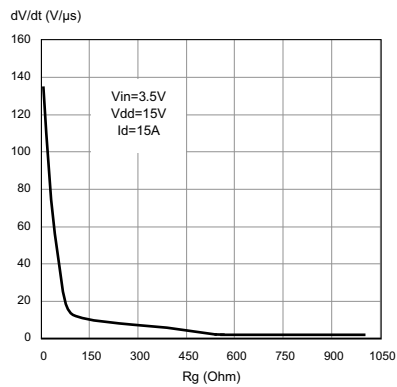


Figure 22. Switching time resistive load (part 1)

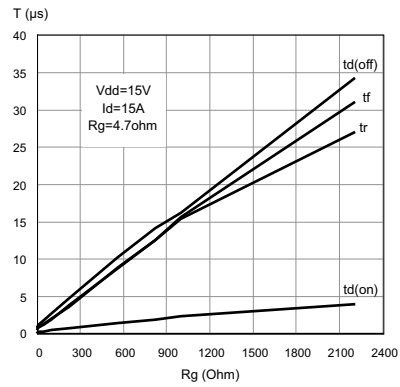


Figure 23. Switching time resistive load (part 2)

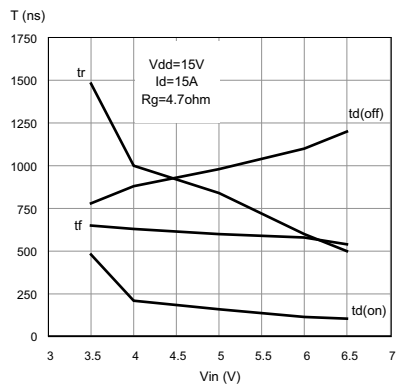


Figure 24. Normalized input threshold voltage vs. temperature

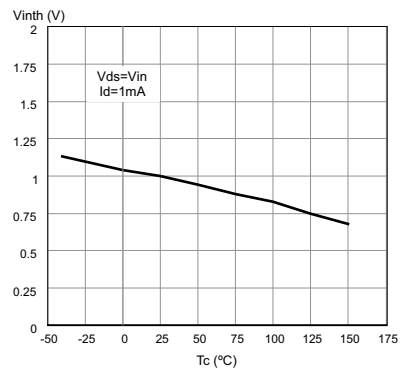


Figure 25. Current limit vs. junction temperature

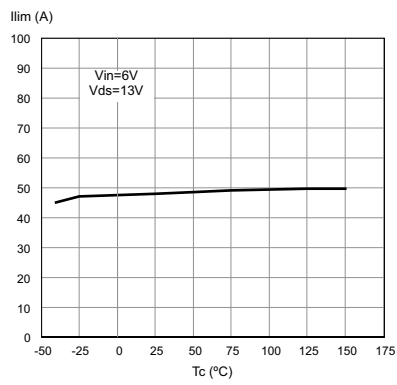
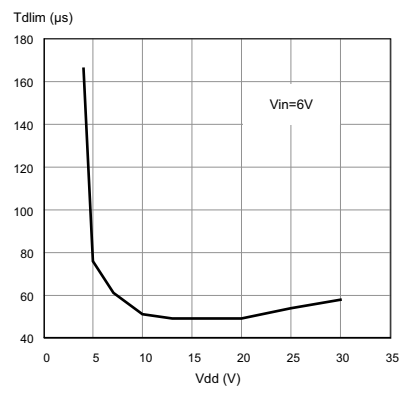
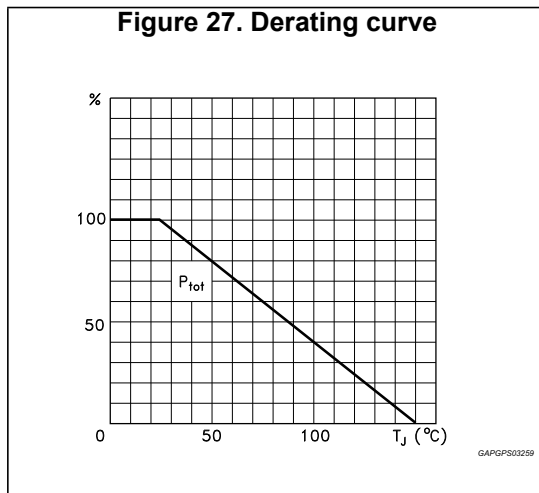


Figure 26. Step response current limit





3 Package information

3.1 ECOPACK®

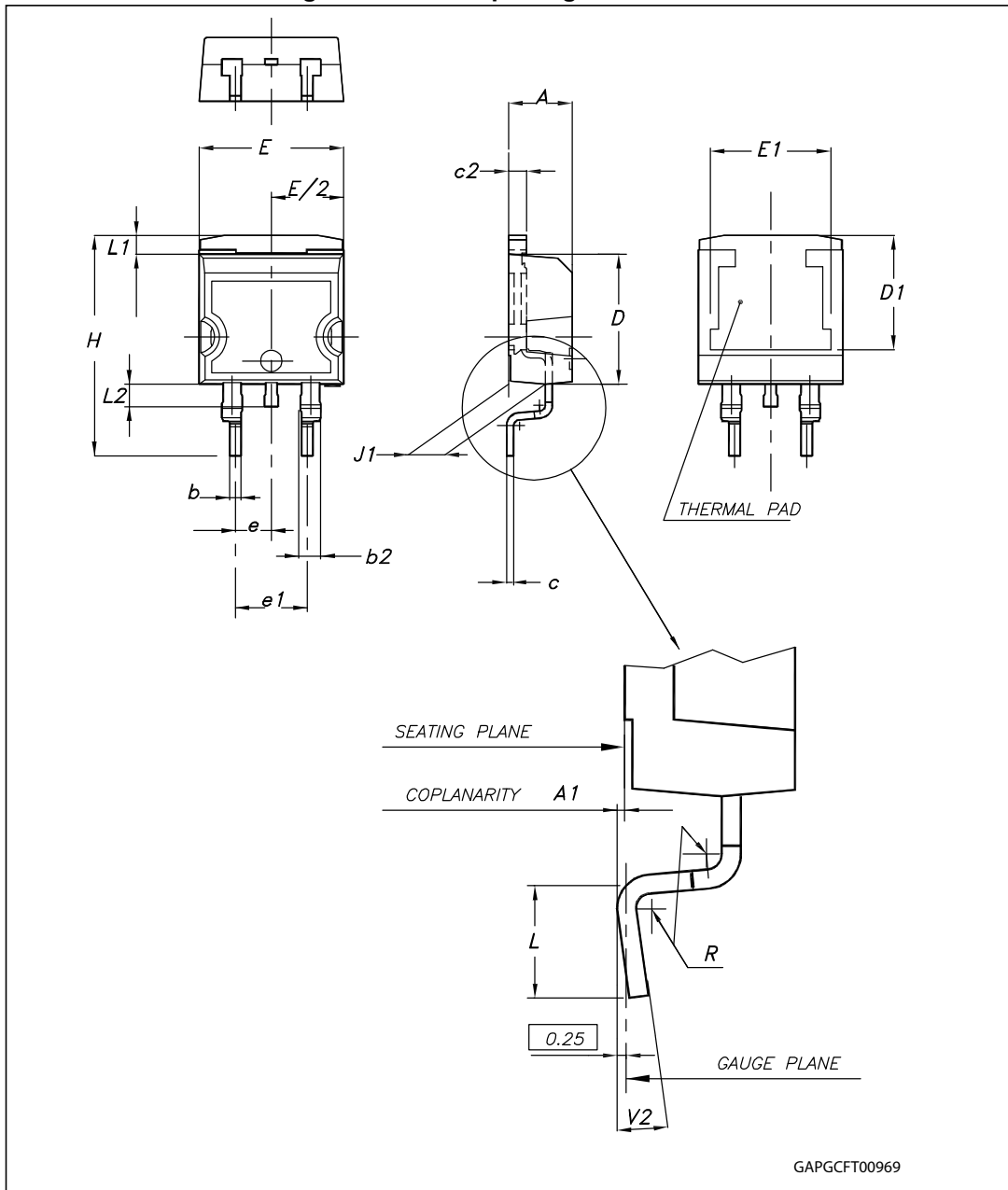
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

3.2 D²PAK mechanical data

Table 10. D²PAK mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 28. D²PAK package dimensions



3.3 D²PAK packing information

Figure 29. D²PAK footprint

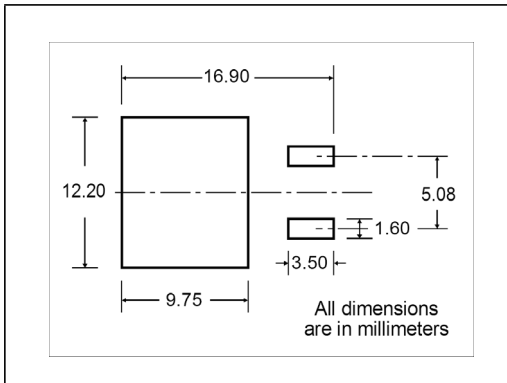


Figure 30. Tube shipment (no suffix)

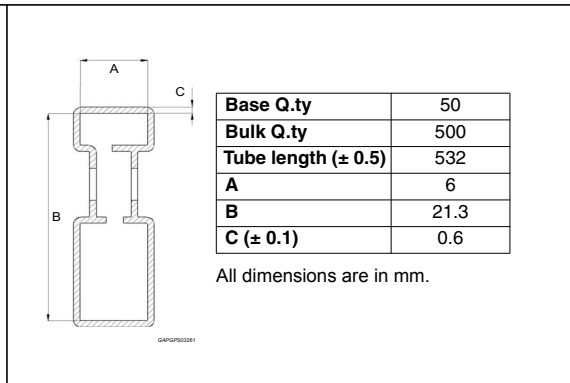
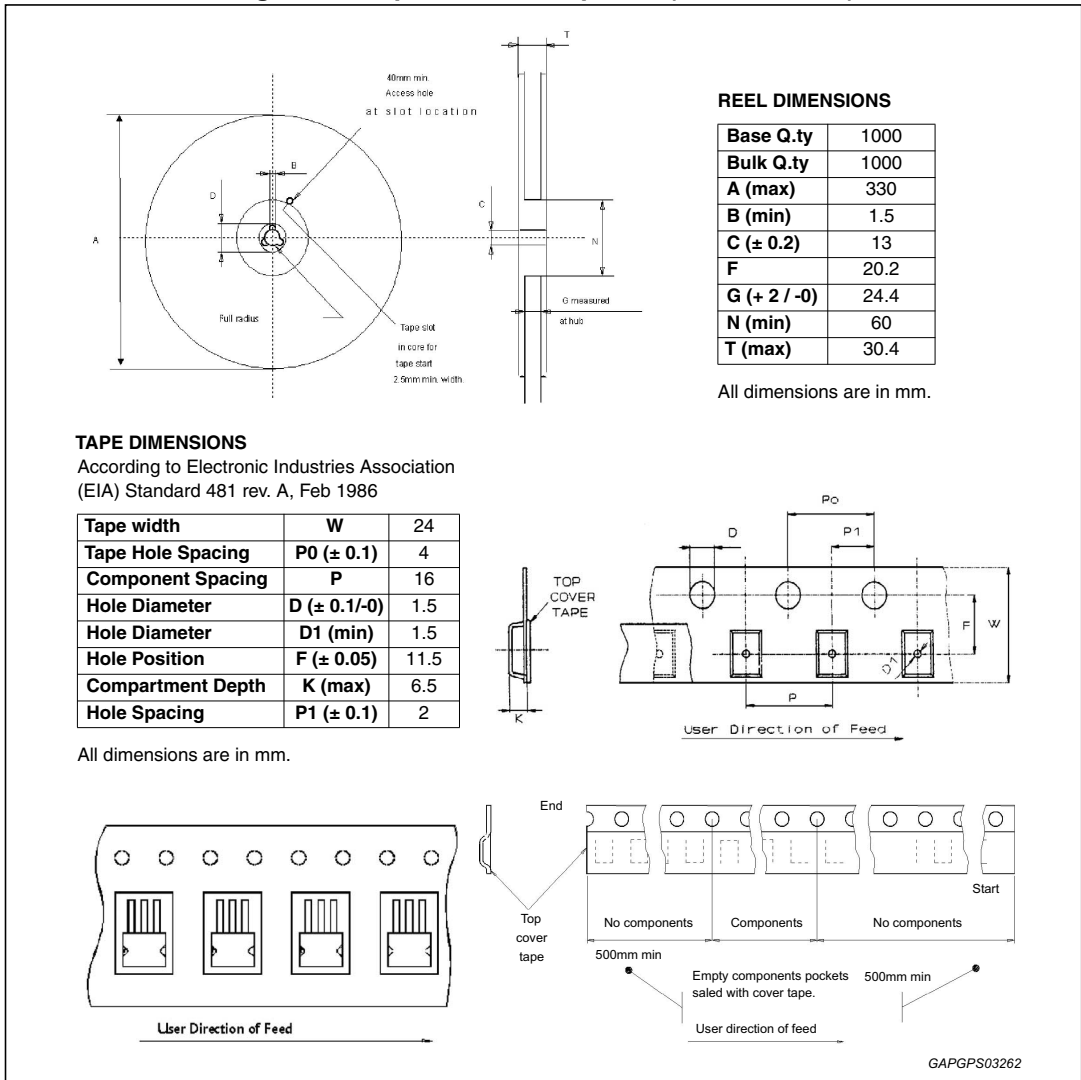


Figure 31. Tape and reel shipment (suffix "13TR")



4 Revision history

Table 11. Document revision history

Date	Revision	Changes
24-Jul-2014	1	Initial release.
16-Sep-2014	2	Updated <i>Features on page 1</i> .

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